

# Thunderbolt™ 电源选择集成电路 (IC)

查询样品: [TPS22985](#)

## 特性

- 2.8 V 至 19.8 V
- 自动选择 3.3 V 电源
- >10-mA 低功率开关
- >500-mA 高功率开关
- 从 OUT 至 VDD 的反向电流阻止
- 通用异步收发器 (UART) 输入活动上唤醒
- UART RX 和 TX 缓冲器

## 应用范围

- Thunderbolt™ 线缆
- 笔记本电脑
- 台式机
- 电源管理系统

## 说明

TPS22985 是一款电源选择器件，此器件用于 Thunderbolt™ 线缆。此器件选择一个 3.3 V 电源，此电源来自两个电源输入并且将此器件连接至两个非电流限制输出 OUTA 和 OUTB。当 3.3 V 电压不出现在任一电源上时，输出变成高阻抗。

TPS22985 有两个运行模式，正常模式和控制模式。

在正常模式下，当一个有效电源出现时，OUTA 一直接通。当 ENB 输入为高电平时，OUTB 被连接至一个有效 VDD。

在控制模式中，OUTA 功能与正常模式下一样而 OUTB 由一个受监控输入和 VDD1 及 VDD2 上的有效输入间的组合控制。当一个有效 VDD 可用时，此器件在 ENB 上等待一个上升输入，然后在下一个下降 RXH 转变到来前，断开 OUTB。一旦下一个下降 RXH 转变发生时，此器件重新连接 OUTB。

在任一模式下，当一个有效 VDD 不可用时，TPS22985 打开所有开关并且输出 OUTA 和 OUTB 编程高阻抗。当被连接的 VDD 超过一个 3.6 V 的最大电压时，它从输出上断开。只有当它处于有效范围内并且 VDD1 大于 3.6 V 时，VDD2 才会连接。

TPS22985 采用一个 1.6mm x 1.6mm 晶圆级芯片 (WCSP) 封装。

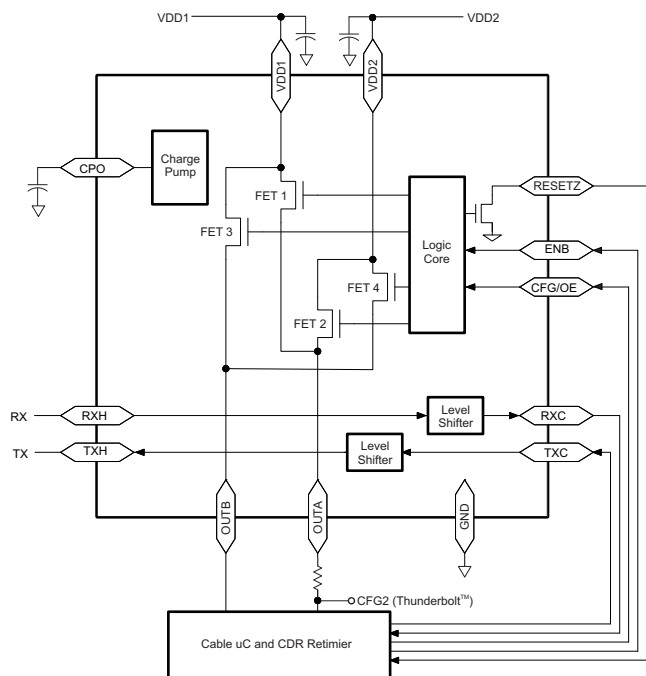


图 1. 典型应用



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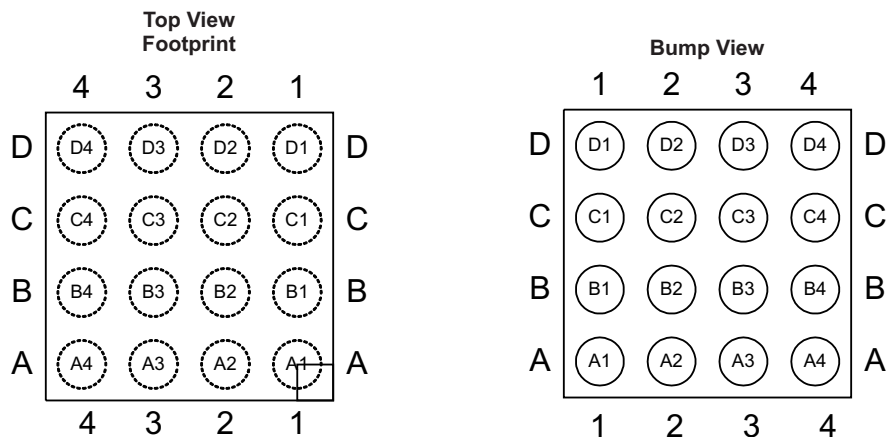


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### ORDERING INFORMATION

PART NUMBER	PACKAGE MARKING <sup>(1)</sup>	PACKAGE	DEVICE SPECIFIC FEATURES
TPS22985YFP	YMD9US	YFP	WCSP

(1) Y= Year, M = Month, D = Sequence Code, 9U = TPS22985 Device Code, S = Wafer Fab/Assembly Site Code



Die Size: 1.6mm x 1.6mm

Bump Size: 0.25mm

Bump Pitch: 0.4mm

**Table 1. TPS22985 Pin Mapping (Top View)**

	4	3	2	1
D	VDD1	VDD1	VDD2	VDD2
C	OUTA	OUTB	OUTB	GND
B	RXH	TXH	RESETZ	CPO
A	RXC	TXC	ENB	CFG/OE

### DISSIPATION RATINGS

PACKAGE	THERMAL RESISTANCE $\theta_{JA}$	THERMAL RESISTANCE <sup>(1)</sup> $\theta_{JB}$	POWER RATING $T_A = 25^\circ\text{C}$	DERATING FACTOR ABOVE <sup>(2)</sup> $T_A = 25^\circ\text{C}$
YFP	95°C/W	63°C/W	1050 mW	10.5 mW/°C

(1) Simulated with high-K board

(2) Maximum power dissipation is a function of  $T_{J(\max)}$ ,  $\theta_{JA}$  and  $T_A$ . The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_{J(\max)} - T_A) / \theta_{JA}$ .

## ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2)</sup>

		VALUE	UNIT
$V_I$	Voltage range on VDD1, VDD2, OUTA, OUTB <sup>(3)</sup>	–0.3 to 20	V
	Voltage range on RXC, TXC, RESETZ, CFG/OE, ENB <sup>(3)</sup> (VDD is the active 3.3V input)	–0.3 to VDD+0.3	V
	Voltage range on CPO	–0.3 to 13	V
	Voltage range on RXH, TXH	–0.3 to 4.0	V
$T_A$	Operating ambient temperature range	–40 to 85	°C
$T_{J(MAX)}$	Maximum operating junction temperature	125	°C
$T_{stg}$	Storage temperature range	–65 to 150	°C
	Charge Device Model (JESD 22 C101)	350	V
	Human Body Model (JESD 22 A114)	2	kV
	Contact discharge on VDD1, VDD2 (IEC 61000-4-2) <sup>(4)</sup>	4.4	kV

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature  $T_{A(max)}$  is dependent on the maximum operating junction temperature  $T_{J(max)}$ , the maximum power dissipation of the device in the application  $P_{D(max)}$ , and the junction-to-ambient thermal resistance of the part/package in the application  $\theta_{JA}$ , as given by the following equation:  $T_{A(max)} = T_{J(max)} - (\theta_{JA} \times P_{D(max)})$
- (3) All voltage values are with respect to network ground terminal.
- (4) IEC tests are run with 0.1  $\mu$ F on VDD1 and VDD2. IEC rating is non-destructive.

## RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
$V_{DD1}$	Supply voltage range		2.8	19.8	V
$V_{DD2}$			2.8	19.8	
$I_{LIM1/2}$	FET1 and FET2 switch current range		0	10	mA
$I_{LIM3/4}$	FET3 and FET4 switch current range		0	500	mA
$V_{IH}$	Input logic high	RXH, TXC, CFG/OE, ENB	2		V
$V_{IL}$	Input logic low	RXH, TXC, CFG/OE, ENB		0.8	V
$V_{OH}$	Output logic high	RXC, TXH, RESETZ	2.25		V
$V_{OL}$	Output logic low	RXC, TXH, RESETZ		0.4	V
$C_{OUT}$	Output capacitance on OUTA		1	4	$\mu$ F
	Output capacitance on OUTB		4	22	
$C_{CPO}$	Output capacitance on CPO		2	10	nF
$T_A$	Operating temperature range		–40	85	°C

## ELECTRICAL CHARACTERISTICS

Unless otherwise noted the specification applies over the  $V_{DD}$  range and operating junction temp  $-40^{\circ}\text{C} \leq T_J \leq 85^{\circ}\text{C}$ . Typical values are for  $V_{DD} = 3.3\text{V}$  and  $T_J = 25^{\circ}\text{C}$

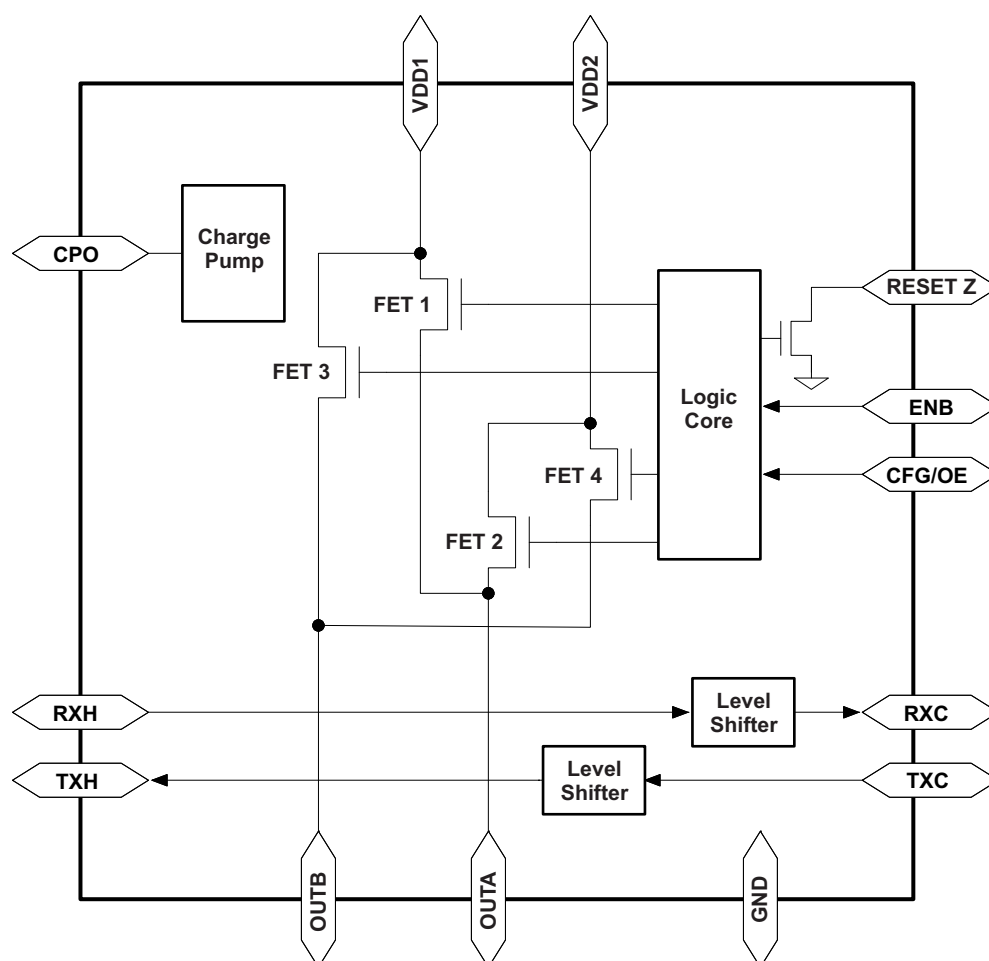
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>POWER SUPPLIES AND CURRENTS</b>						
$V_{DD1/2}$	Input voltage range		2.8		19.8	V
$I_{DD-1}$	VDD1 Quiescent current	$V_{DD1} = 2.5 \text{ to } 15 \text{ V}$		250	500	$\mu\text{A}$
$I_{DD-2}$	VDD2 Quiescent current	$V_{DD2} = 3.3 \text{ V}, V_{DD1} = 3.3 \text{ V}$		20		$\mu\text{A}$
		$V_{DD2} = 3.3 \text{ V}, V_{DD1} = 15 \text{ V}$		20		
$I_{DDOFF-2}$	VDD2 Off current	$V_{DD2} = 3.3 \text{ V}, V_{DD1} = 0 \text{ V}$			1	$\mu\text{A}$
$I_{IN-ENB}$	ENB Input current	$V_{IN} = 1.8 \text{ V to } 3.6 \text{ V}$			1	$\mu\text{A}$
$I_{IN-UART}$	RXH Input current	$V_{IN} = 1.8\text{V to } 3.6 \text{ V}$			1	$\mu\text{A}$
$I_{IN-CFGOE}$	CFG/OE Input current <sup>(1)</sup>	$V_{CFG/OE} = 0 \text{ V}$	-1	-1.8	-5	$\mu\text{A}$
$V_{PUCFGOE}$	CFG/OE pull-up voltage <sup>(1)</sup>		2.3		6.7	V
$I_{IN-RESETZ}$	RESETZ Input current	$V_{RESETZ} = 100 \text{ mV}$	0.8	2	3	mA
<b>SWITCH AND RESISTANCE CHARACTERISTICS</b>						
$R_{F1}$	FET1 On resistance	$V_{DD} = 3.3 \text{ V}, I_{OUT} = 10 \text{ mA}$			5	$\Omega$
$R_{F2}$	FET2 On resistance				5	
$R_{F3}$	FET3 On resistance	$V_{DD} = 3.3 \text{ V}, I_{OUT} = 350 \text{ mA}$		170	250	m $\Omega$
$R_{F4}$	FET4 On resistance			170	250	
$R_{PDRESETZ}$	RESETZ Pull-down resistance	RESETZ asserted	33	50	100	$\Omega$
$R_{PUCFGOE}$	CFG/OE Pull-up resistance <sup>(1)</sup>		1.2	2	2.6	M $\Omega$
$R_{PDUART}$	TXC Pull-down resistance	See the UART RX and TX Section	80	130	180	k $\Omega$
<b>VOLTAGE THRESHOLDS AND AMPLITUDES</b>						
$V_{HVLO}$	High voltage lockout	3.3V Supply rising	3.5	3.55	3.6	V
	Hysteresis		20	40	60	mV
$V_{UVLO}$	Under voltage lockout	3.3V Supply rising	2.7	2.75	2.8	V
		3.3V Supply falling	2.4	2.45	2.5	
$V_{CPO}$	Charge pump voltage	$C_{CPO} = 2 \text{ nF}, I_{CPO} = 0 \mu\text{A}$	7	8	9	V
$V_{OS}$	Voltage overshoot on OUTA/B	$C_{OUTB} = 4 \mu\text{F}, I_{OUTB} = 0 \text{ mA},$ $C_{OUTA} = 1 \mu\text{F}, I_{OUTA} = 0 \text{ mA}$ $V_{DD1} \text{ SR}_{3.3 \rightarrow 4\text{V}} = 10 \text{ mV}/\mu\text{s}$			200	mV

(1) CFG/OE is pulled up to  $V_{PUCFGOE}$  through the resistance  $R_{PUCFGOE}$ .

## ELECTRICAL CHARACTERISTICS (continued)

Unless otherwise noted the specification applies over the  $V_{DD}$  range and operating junction temp  $-40^{\circ}\text{C} \leq T_J \leq 85^{\circ}\text{C}$ . Typical values are for  $V_{DD} = 3.3\text{V}$  and  $T_J = 25^{\circ}\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
THERMAL SHUTDOWN							
T <sub>SD</sub>	Shutdown temperature			110		130	°C
T <sub>SDHYST</sub>	Shutdown hysteresis				15		°C
TRANSITION TIMING							
t <sub>d</sub>	UVLO to FETn open time	C <sub>OUTB</sub> = 4 μF, C <sub>OUTA</sub> = 1 μF			200		μs
t <sub>e</sub>	UVLO to FETn closed time				2		ms
t <sub>dh</sub>	HVLO to FETn open time				20		μs
t <sub>eh</sub>	HVLO to FETn closed time	See The Supply Switch-Over During HVLO Section					
TRANSITION TIMING (NORMAL MODE)							
t <sub>eb</sub>	ENB to FET3/4 closed time	C <sub>OUTB</sub> = 4 μF, C <sub>OUTA</sub> = 1 μF			2		ms
t <sub>db</sub>	ENB to FET3/4 open time				200		μs
TRANSITION TIMING (CONTROL MODE)							
t <sub>U2R</sub>	UVLO to RESETZ time			5	6	7	ms
t <sub>E2R</sub>	ENB to RESETZ time				2	10	μs
t <sub>E2O</sub>	ENB to FET3/4 open time	C <sub>OUTB</sub> = 4 μF, C <sub>OUTA</sub> = 1 μF			100	200	μs
t <sub>RX2O</sub>	RX to FET3/4 closed time	C <sub>OUTB</sub> = 4 μF, C <sub>OUTA</sub> = 1 μF			0.8	2	ms
t <sub>RX2R</sub>	RX to RESETZ Time			5	6	7	ms
t <sub>OE2TX</sub>	OE to TXH Valid Time					20	μs
t <sub>OE2TXZ</sub>	OE to TXH Hi-Z Time					20	μs
TXC/TXH I/O (CONTROL MODE)							
V <sub>IH</sub>	TXC Input logic high			2			V
V <sub>IL</sub>	TXC Input logic low					0.8	V
V <sub>OH</sub>	TXH Output logic high			2.25			V
V <sub>OL</sub>	TXH Output logic low					0.4	V
T <sub>R</sub> / T <sub>F</sub>	TXH Rise and fall time	10-90% CL = 20 pF		5		70	ns
Z <sub>O</sub>	TXH Output impedance				35		Ω
f <sub>MAX</sub>	TX Input signal frequency					1	Mb/s
DC	TX Duty cycle			40%		60%	
RXC/RXH I/O (CONTROL MODE)							
V <sub>IH</sub>	RXH Input logic high			2			V
V <sub>IL</sub>	RXH Input logic low					0.8	V
V <sub>OH</sub>	RXC Output logic high			2.25			V
V <sub>OL</sub>	RXC Output logic low					0.4	V
T <sub>R</sub> / T <sub>F</sub>	RXC Rise and fall time	10-90% CL = 20 pF		20		120	ns
f <sub>MAX</sub>	RX Input signal frequency					1	Mb/s
DC	RX Duty cycle			40%		60%	

**FUNCTIONAL BLOCK DIAGRAM****Figure 2. Functional Block Diagram**

## DEVICE INFORMATION

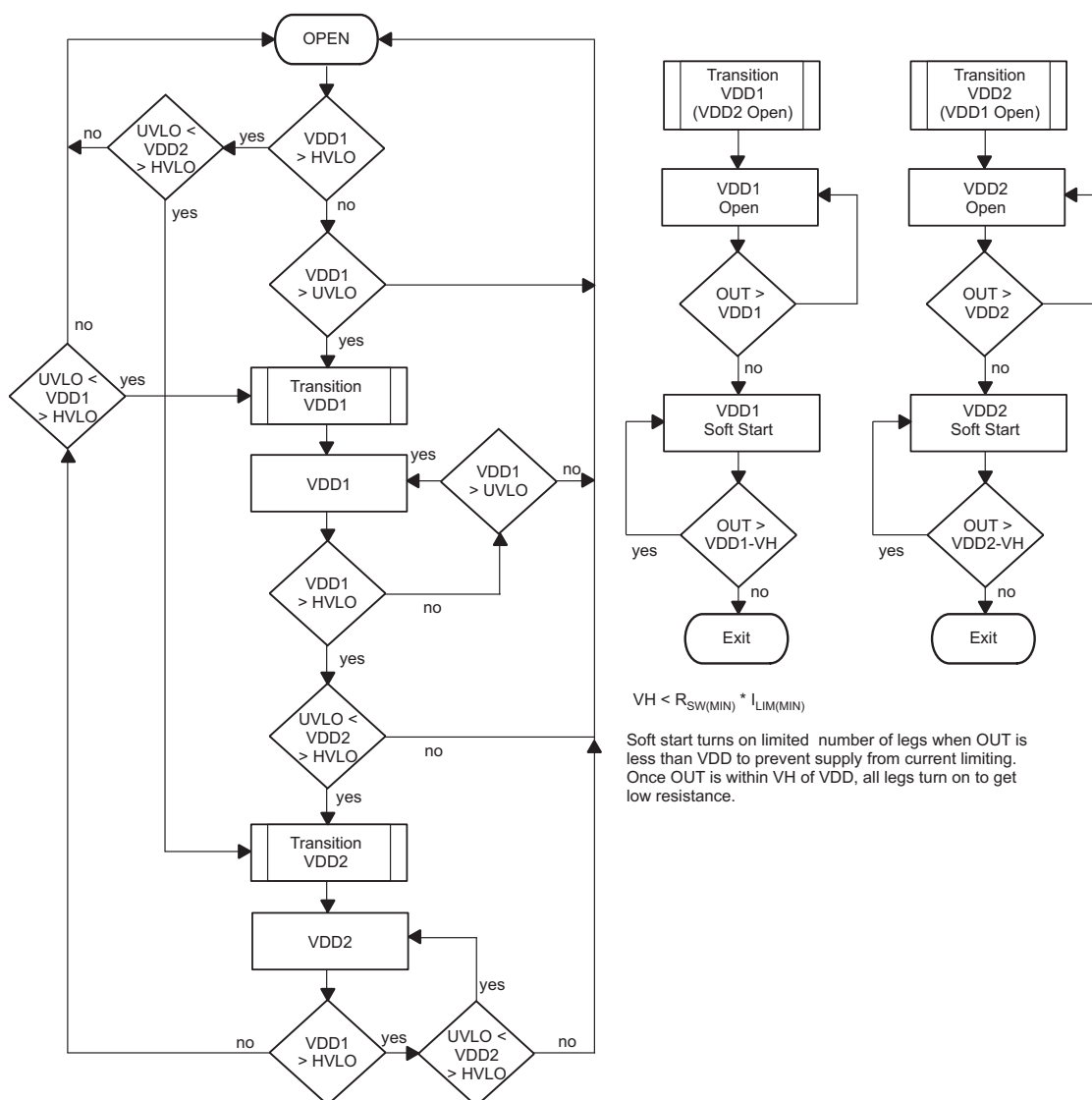
### PIN FUNCTIONS

PIN NAME	TYPE	DESCRIPTION
VDD1	Supply	<b>Device Supply 1.</b> 0V to 19.8-V Input.
VDD2	Supply	<b>Device Supply 2.</b> 0V to 19.8-V Input.
OUTA	Output	<b>Output A.</b> 10-mA capable output. Refer to the <a href="#">Supply Selection</a> section for more information.
OUTB	Output	<b>Output B.</b> 500-mA capable output. Refer to the <a href="#">Normal Mode</a> and <a href="#">Control Mode</a> sections for more information.
CPO	Output	<b>Charge Pump Output.</b> This pin is the output of the internal charge pump. It drives the gates of the internal FET switches. Connect a capacitor of at least 2nF to this pin.
CFG/OE	Input	<b>Mode Configuration/Output Enable.</b> When CFG is floating, the device is in Normal Mode. When CFG is ground, the device is in Control Mode (see the <a href="#">APPLICATION INFORMATION</a> section for more information). The mode is latched at power-up. When the device enters Control Mode, this pin becomes an output enable for the UART TXH output. See the <a href="#">UART RX and TX</a> section for more information. A pull-down resistance between this pin and GND is recommended when Control Mode is desired.
RXH	Input	<b>UART RX Input.</b> Monitored Input for data activity to enable outputs. In Control Mode, this pin is monitored for a high to low transition to enable the outputs. This input is level shifted and driven on RXC. See the <a href="#">UART RX and TX</a> section for more information.
RXC	Output	<b>UART RX Output.</b> This output is a level shifted version of RXH. RXC is referenced to OUTA. See the <a href="#">UART RX and TX</a> section for more information.
TXC	Input	<b>UART TX Input.</b> This input is buffered and level shifted on TXH. See the <a href="#">UART RX and TX</a> section for more information.
TXH	Output	<b>UART TX Output.</b> This output is a buffered and level shifted version of TXC. TXH is referenced to OUTA. See the <a href="#">UART RX and TX</a> section for more information.
RESETZ	Output	<b>Microcontroller Reset.</b> This pin is a delayed reset signal indicating OUTB is connected to a valid VDD. RESETZ in an open-drain pull-down. RESETZ is low when OUTB is high impedance.
ENB	Input	<b>OUTB Enable.</b> In Normal Mode, this pin is the active high OUTB enable. In Control Mode, this pin opens OUTB when asserted high and resets the device until a new transition on RX occurs.
GND	Supply	<b>Device ground.</b>

## APPLICATION INFORMATION

### Supply Selection

The TPS22985 selects between two separate power supplies, VDD1 or VDD2, and connects these to two outputs (OUTA and OUTB) through non-current limited switches. When a valid VDD ( $V_{UVLO} < VDD < V_{HVLO}$ ) is present on VDD1, VDD1 will be connected to the outputs. When  $VDD1 > V_{HVLO}$ , the TPS22985 will connect the outputs to VDD2 when a valid VDD is present on this input. OUTB is also opened and closed by other digital inputs, ENB and RXH, depending on the mode of the TPS22985. Refer to the [Normal Mode](#) and [Control Mode](#) sections for more information on the control of OUTB. VDD1 and VDD2 can power up in any order; however, VDD1 always takes priority over VDD2 and only allows VDD2 to connect when the  $VDD1 > V_{HVLO}$  condition is present. When the outputs are connected to VDD2, and VDD1 drops below  $V_{HVLO}$ , the TPS22985 will disconnect the outputs from VDD2. [Figure 3](#) shows a flow diagram illustrating the selection of VDD1 or VDD2 as the appropriate supply to connect to OUTA and OUTB. Note, this diagram does not show the enabling and disabling of OUTB by ENB and RXH.



**Figure 3. Flow Diagram of Supply Selection and Switch-Over**



## Normal Mode

When the CFG/OE pin is floating at power-up, the device enters Normal Mode. In Normal Mode, the TPS22985 provides power via OUTA and OUTB.

OUTA is connected whenever a valid VDD is present on VDD1. OUTA may also be connected if  $VDD1 > V_{HVLO}$  and a valid VDD is connected to VDD2. OUTB is connected whenever a valid VDD is present on VDD1. OUTB may also be connected if  $VDD1 > V_{HVLO}$ , a valid VDD is connected to VDD2, and the control signal ENB is high. When OUTB is connected it will supply  $\geq 500$  mA to a load.

When a valid VDD is not present, the TPS22985 enters into a shutdown mode and blocks current flow through the switches.

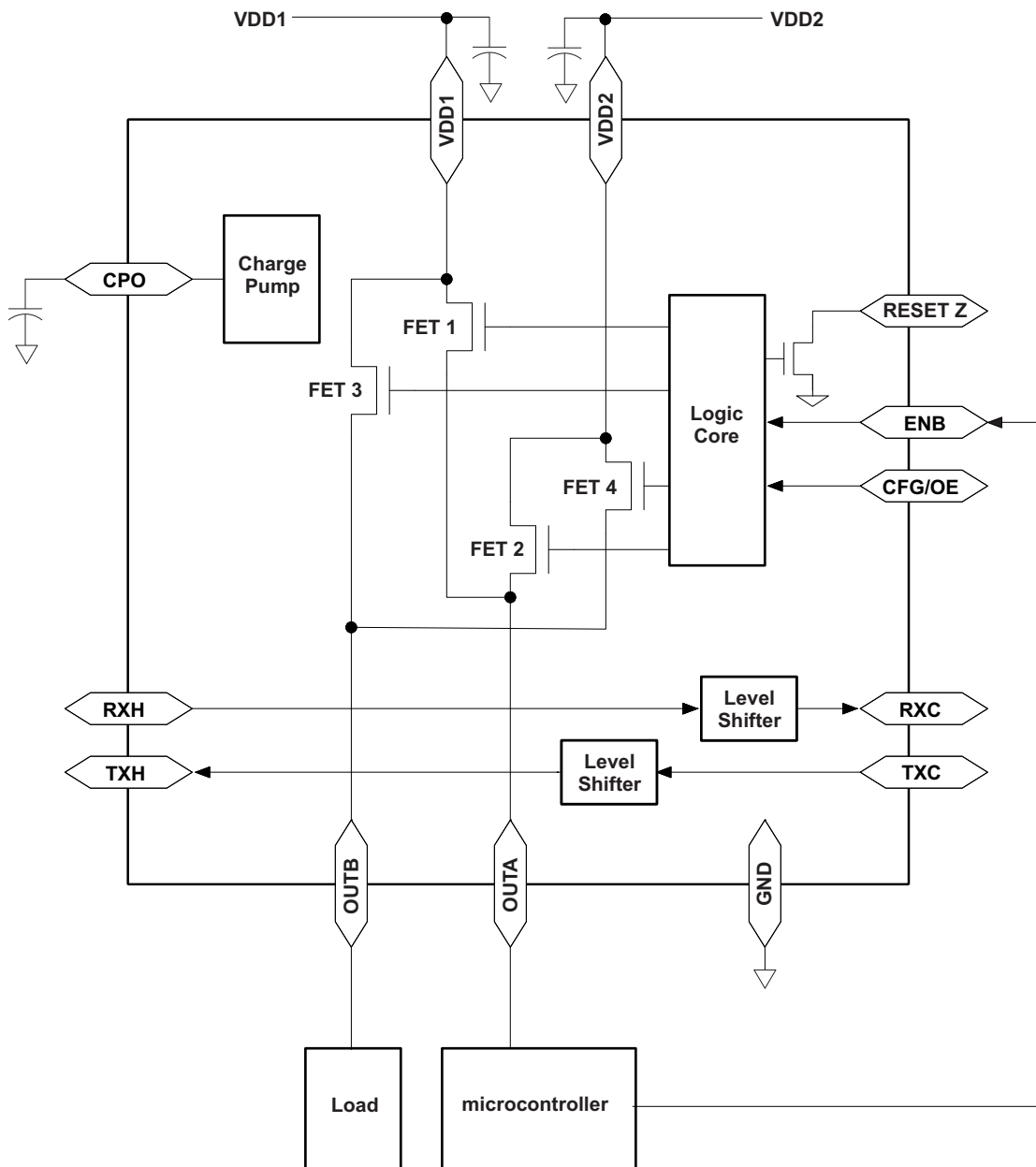


Figure 4. Normal Mode Typical Application

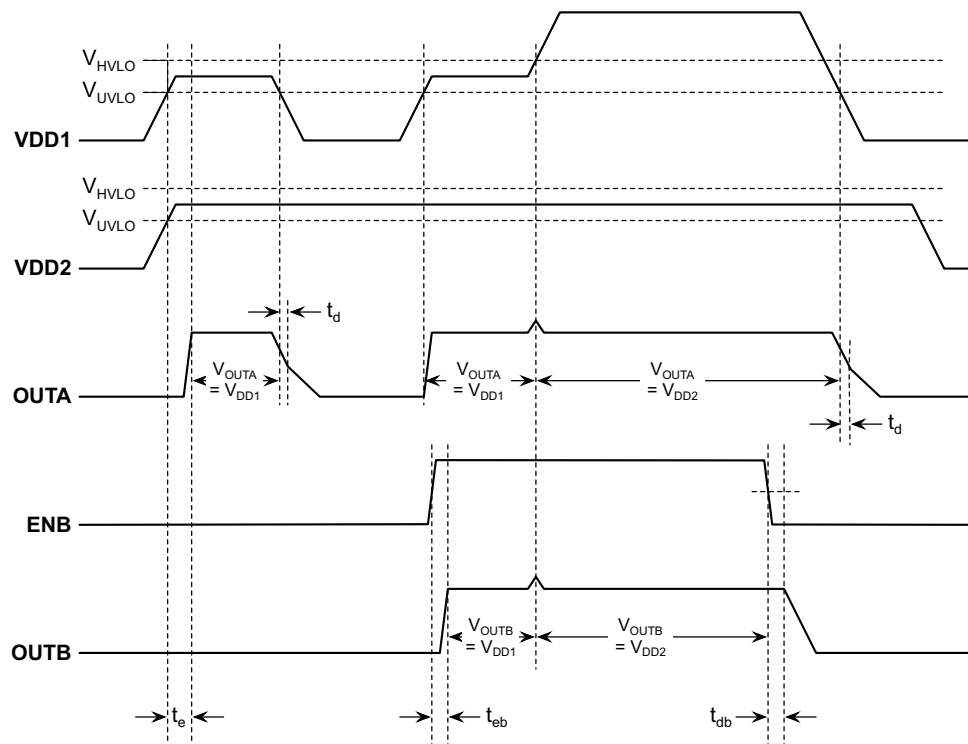


Figure 5. Timing During Normal Mode



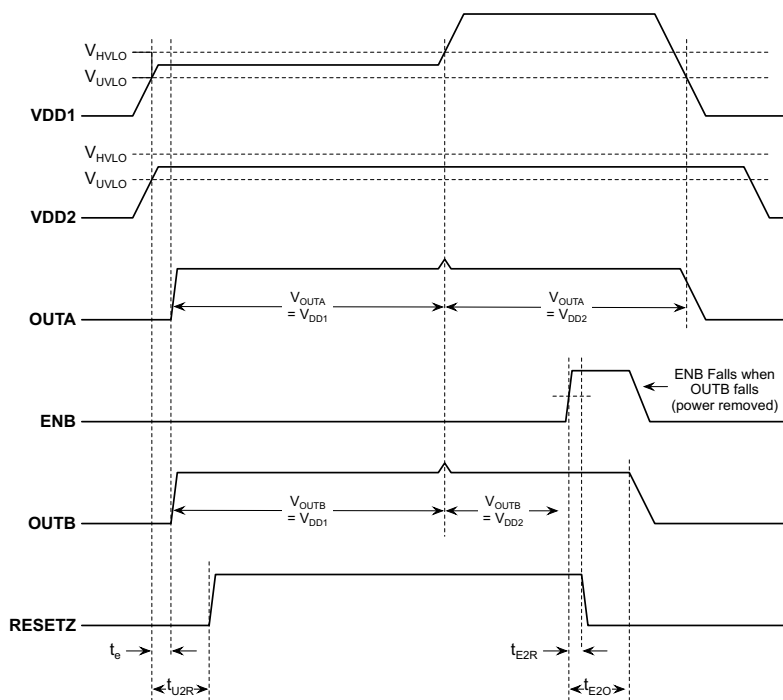


Figure 7. Timing During Control Mode

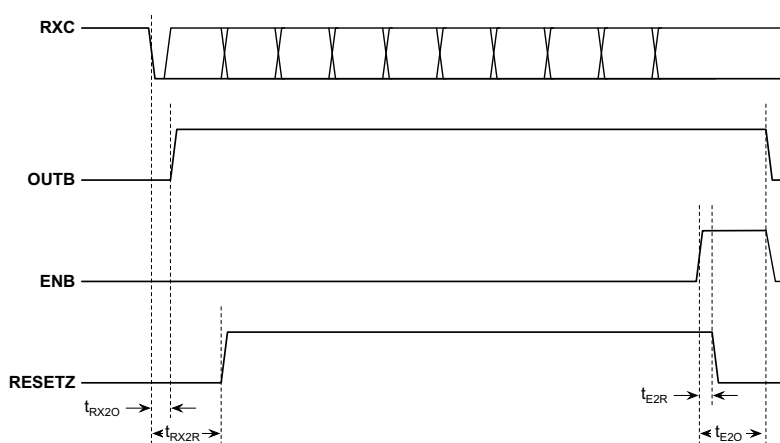
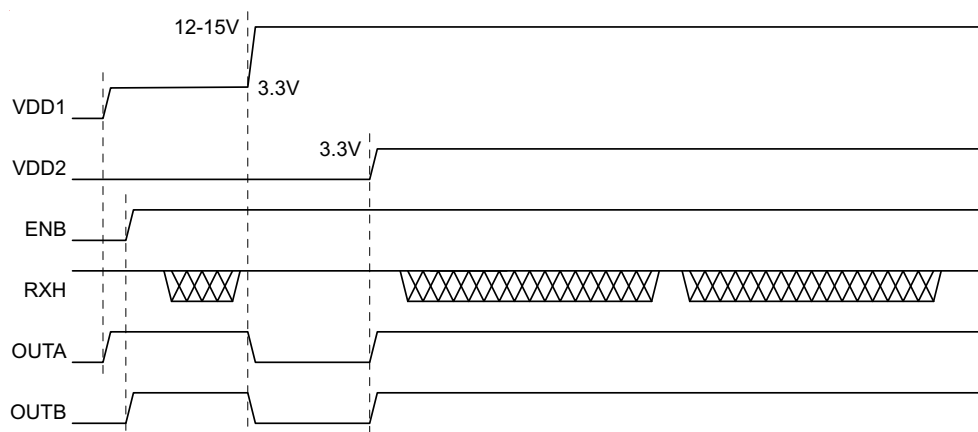
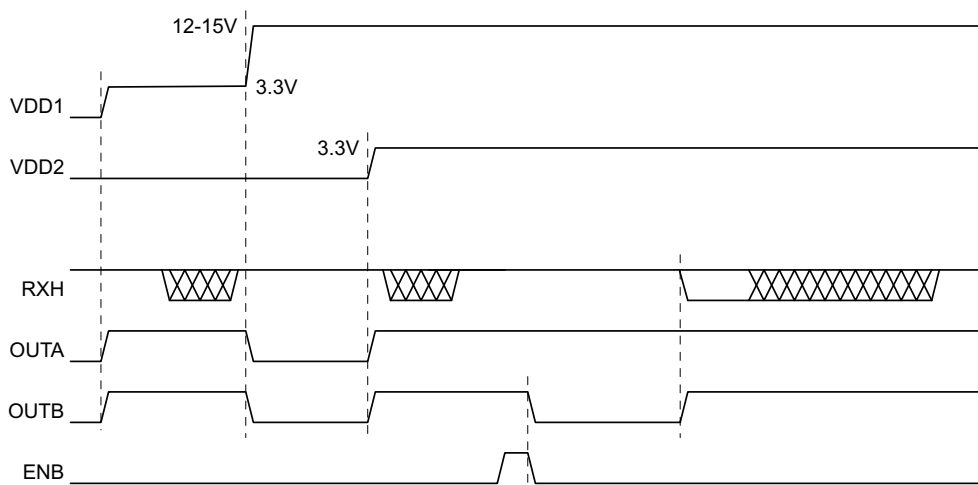


Figure 8. Timing During Control Mode Continued

## Typical Startup



**Figure 9. Typical Startup in Normal Mode**



**Figure 10. Typical Startup Timing for Control Mode**

**Figure 10. Typical Startup Timing for Control Mode**

## Soft Start

To prevent inrush current to the load, the TPS22985 soft starts OUTA and OUTB. When OUTA and OUTB are first enabled, the resistance of the FET switches (FET1, FET2, FET3, and FET4) starts high and reduces every 250 $\mu$ s in four steps. [Figure 11](#) shows the nominal resistance ramp profile for OUTB. The resistance shown in this figure is the equivalent resistance through FET3 and FET4 in [Figure 2](#).

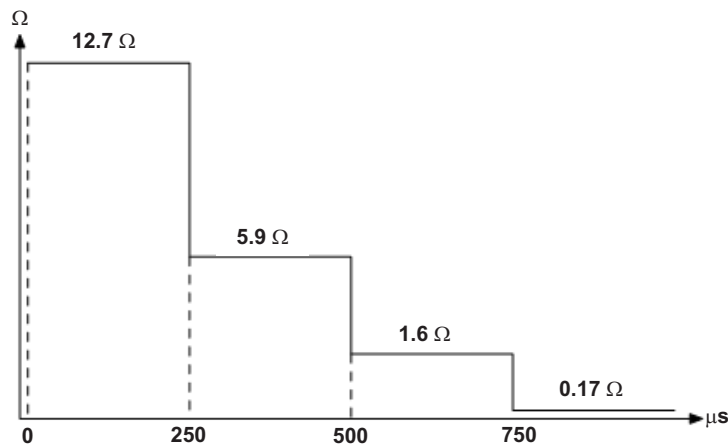


Figure 11. OUTB Soft Start Resistance vs Time Profile

## Supply Switch-Over During HVLO

When OUTA and OUTB are connected to VDD1 and VDD1 crosses  $V_{HVLO}$ , the TPS22985 will open the FET1/3 switches. Due to the delay  $t_{dh}$ , the output will overshoot  $V_{HVLO}$  by  $V_{OS}$ . When a valid VDD is present on VDD2, OUTA and OUTB will connect to VDD2 after time  $t_{eh}$ . Figure 12 illustrates this switch-over event.

The overshoot  $V_{OS}$  will occur when the VDD (VDD1 or VDD2) that is connected to the output transitions above  $V_{HVLO}$ .  $V_{OS}$  is set by the delay  $t_{dh}$  and the slew rate of the connected VDD. However, the connection of the outputs to VDD2 will only occur when VDD1 transitions above  $V_{HVLO}$  and VDD2 is a valid VDD.

The following equation determines the overshoot  $V_{OS}$ .

$$V_{OS} = SR_{VDD} \times t_{DH} \quad (1)$$

$SR_{VDD}$  is the slew rate of the supply that is transitioning above  $V_{HVLO}$ . As an example, when  $SR_{VDD}$  is 10mV/ $\mu$ s and  $t_{dh}$  is 20 $\mu$ s,  $V_{OS}$  is 200mV.

When switching to VDD2 due to an HVLO event on VDD1, the outputs OUTA and OUTB are discharged by their respective loads until they reach the VDD2 voltage. This prevents in-rush current when charging the output caps. The discharge time  $t_{eh}$  is variable and is determined by the following equation.

$$t_{eh} = t_{dh} + (V_{HVLO} + V_{OS} - V_{DD2}) \times C_{LOAD} / I_{LOAD} \quad (2)$$

In this equation,  $V_{OS}$  is determined by Equation 1,  $C_{LOAD}$  is the load capacitance at the respective output, and  $I_{LOAD}$  is load current flowing out of the same output. As an example, when VDD2 is 3.3V,  $t_{dh}$  is 20 $\mu$ s,  $V_{OS}$  is 200mV,  $C_{LOAD}$  is 4 $\mu$ F, and  $I_{LOAD}$  is 350mA, the resulting  $t_{eh}$  is 25.7 $\mu$ s.

Note, when VDD1 transitions above  $V_{HVLO}$  and a valid VDD is not present on VDD2, the outputs will open and will discharge through each respective load.

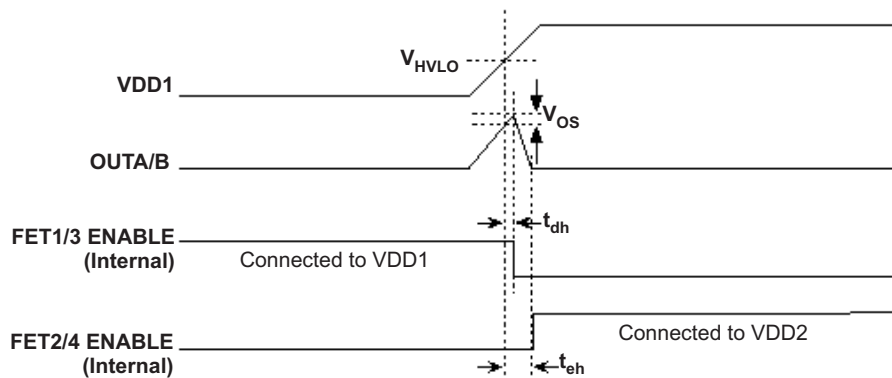


Figure 12. VDD switch-over at VDD1 rising above  $V_{HVLO}$

## UART RX and TX

The TPS22985 provides failsafe buffers for digital UART RX and TX lines. The failsafe mechanism prevents the RX and TX lines from being loaded when power is removed from the device. The RX line is divided into a host side RXH input and a cable side RXC output. The TX line is divided into host side TXH output and a cable side TXC input.

The RXH and TXC inputs are used in Control Mode only and must be pulled low when the device is in Normal Mode. In Normal Mode, leave the RXH and TXC pins disconnected from the UART signal lines and pull low through a  $> 1k\Omega$  resistance.

In Control Mode, when the TPS22985 is unpowered or when RESETZ is asserted low, the TXH output is high impedance. This prevents loading the system TX line and allowing other devices on the UART bus to communicate. The RXC output is pulled low through the output driver during this same condition.

Figure 13 illustrates the RXC and TXH control when in Control Mode. When RESETZ is high, CFG/OE controls TXH. When CFG/OE is low, TXH is high impedance. When CFG/OE is high, TXH is a buffered and level-shifted TXC. The CFG/OE, ENB, and TXC inputs are ignored when RESETZ is asserted low. Figure 14 shows the delay from CFG/OE to TXH.

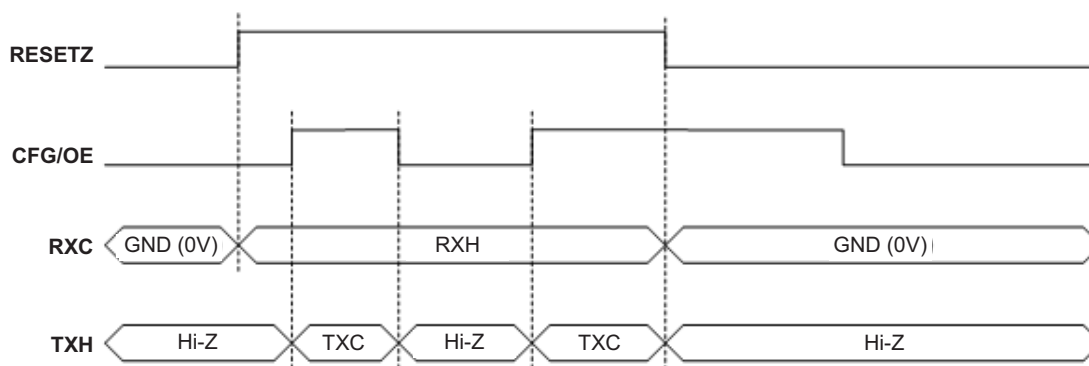


Figure 13. UART RX and TX Buffer Control During Control Mode

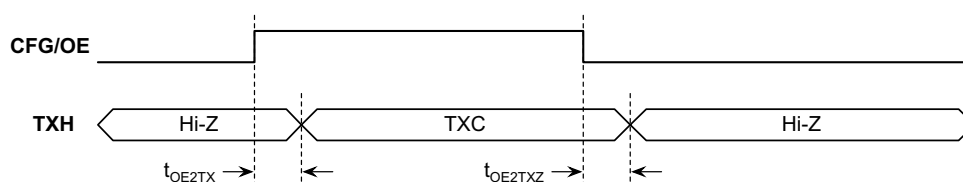
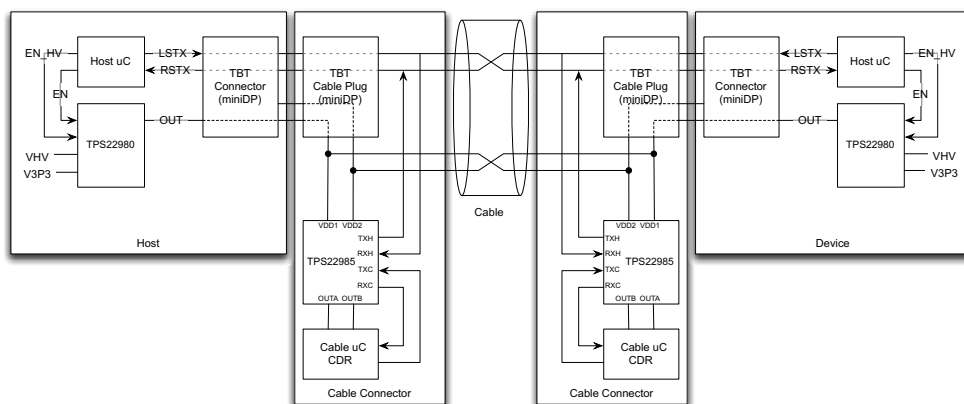


Figure 14. CFG/OE to TXH Timing During Control Mode



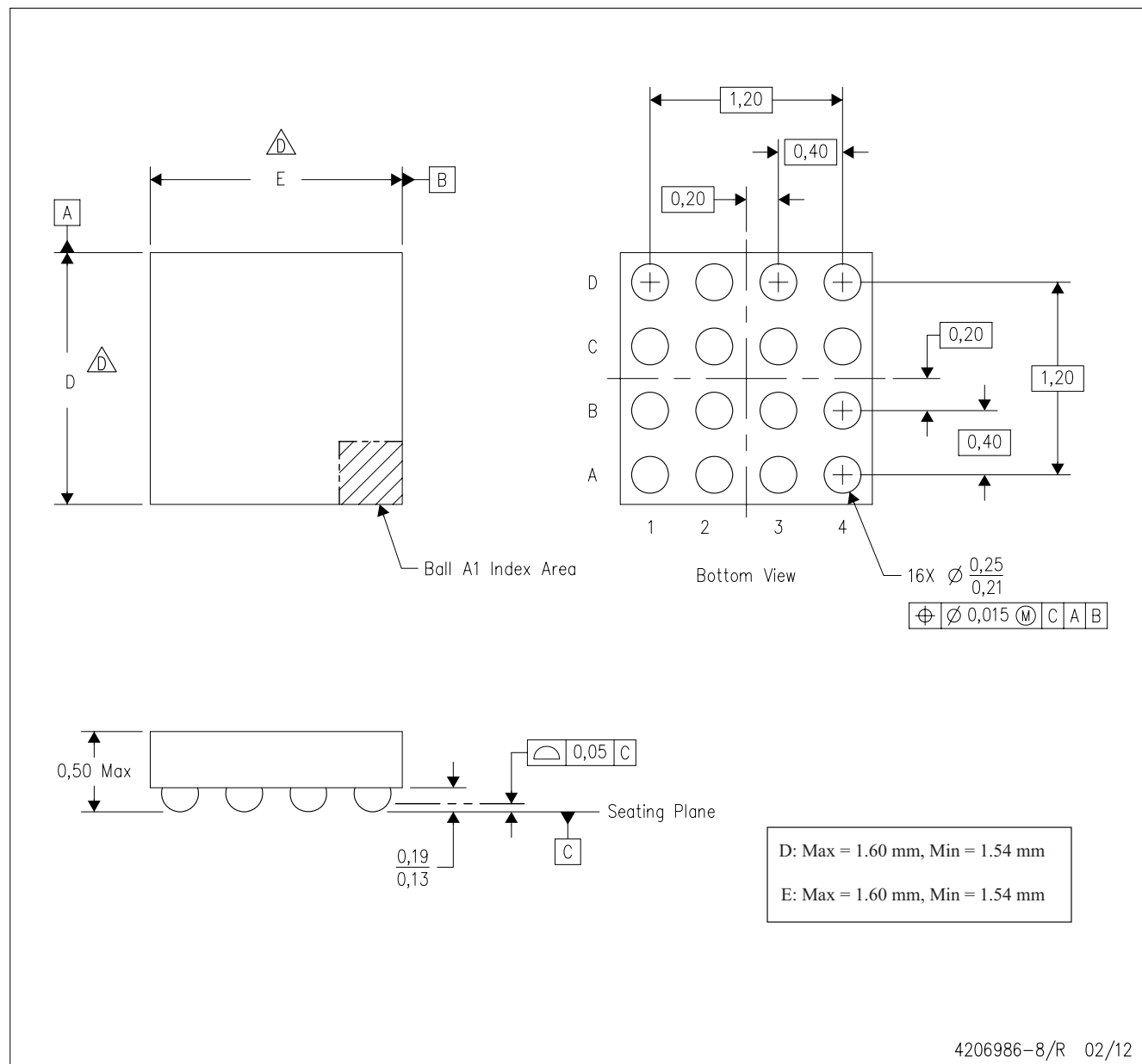
## THUNDERBOLT™ SYSTEM WITH TPS22980/TPS22985



**Figure 15. Thunderbolt System with TPS22980/TPS22985**

YFP (S-XBGA-N16)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - This drawing is subject to change without notice.
  - NanoFree™ package configuration.
  - The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.
  - Reference Product Data Sheet for array population.  
4 x 4 matrix pattern is shown for illustration only.
  - This package contains Pb-free balls.

NanoFree is a trademark of Texas Instruments

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22985YFPR	NRND	DSBGA	YFP	16	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	9U	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22985YFPR	DSBGA	YFP	16	3000	180.0	8.4	1.71	1.71	0.81	4.0	8.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22985YFPR	DSBGA	YFP	16	3000	182.0	182.0	20.0

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